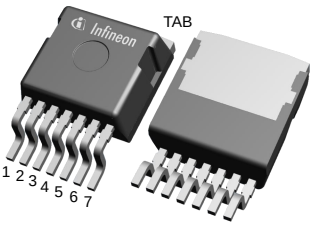
## Final datasheet

## CoolSiC™ 1200 V SiC Trench MOSFET : Silicon Carbide MOSFET




Halogen-free

Green

Lead-free

RoHS

### Features

- $V_{DSS}$ = 1200 V at $T_{vj}$ = 25°C
- $I_{DDC}$ = 70 A at $T_c$ = 25°C
- $R_{DS(on)}$ = 30 mΩ at $V_{GS}$ = 18 V, $T_{vj}$ = 25°C
- New performance-optimized chip technology (Gen1p) with improved $R_{DSon}$* A
- Best-in-class switching energy for lower switching losses and reduced cooling efforts
- Lowest device capacitances for higher switching speeds and higher power density
- A combination of low $C_{rss}/C_{iss}$ ratio and high $V_{GS(th)}$ to avoid parasitic turn-on and enable unipolar gate driving
- Reduced total gate charge $Q_G$ for lower driving power and losses
- Increased recommended turn-on voltage ($V_{GS(on)}$ = 20 V) for lower $R_{DS(on)}$
- .XT die attach technology for best-in-class thermal performance
- Low package stray inductance for faster and cleaner switching
- Sense (Kelvin) source pin for better gate control and reduced switching losses
- Creepage distance of 5.8 mm (material group II) to fit 800 V applications
- SMT package for automated assembly and reduced system costs

### Potential applications

- On-board charger
- DC/DC converter
- Auxiliary drives

### Product validation

- Qualified for Automotive Applications. Product Validation according to AEC-Q100/101

### Description

Pin definition:

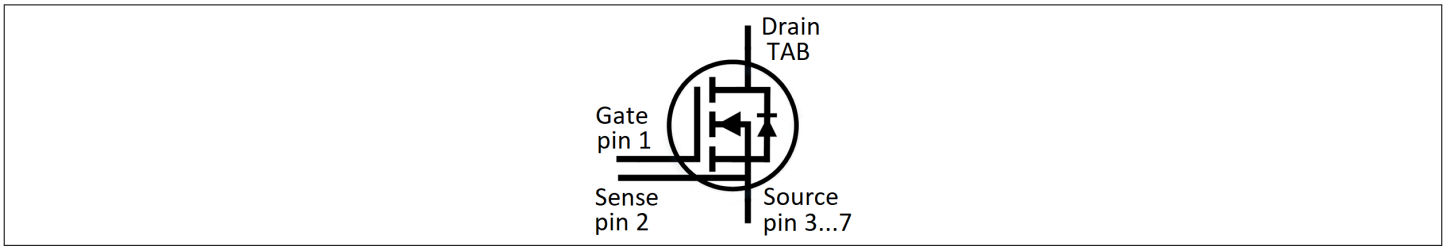
• Pin 1 - Gate

• Pin 2 - Kelvin sense contact

• Pin 3…7 - Source

• Tab - Drain

Note: The source and sense pins are not exchangeable, their exchange might lead to malfunction




| Type | Package | Marking |
|---|---|---|
| AIMBG120R030M1 | PG-TO263-7-U01 | AS30MM1 |



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# 1 Package

**Table 1 Characteristic values**

| Parameter | Symbol | Note or test condition | Values | | | Unit |
|---|---|---|---|---|---|---|
| | | | Min. | Typ. | Max. | |
| Storage temperature | $T_{stg}$ | | -55 | | 150 | °C |
| Soldering temperature | $T_{sold}$ | | | | 260 | °C |
| MOSFET/body diode thermal resistance, junction-case[1)] | $R_{th(j-c)}$ | | | 0.35 | 0.45 | K/W |

1) not subject to production test - verified by design/characterization

# 2 MOSFET

**Table 2 Maximum rated values**

| Parameter | Symbol | Note or test condition | | Values | Unit |
|---|---|---|---|---|---|
| Drain-source voltage[1)] | $V_{DSS}$ | $T_{vj}$ = -55...175 °C | | 1200 | V |
| Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$[2)] | $I_{DDC}$ | $V_{GS}$ = 20 V | $T_c$ = 25 °C | 70 | A |
| | | | $T_c$ = 100 °C | 50 | |
| Peak drain current, $t_p$ limited by $T_{vj(max)}$[2)] | $I_{DM}$ | $V_{GS}$ = 20 V | | 180 | A |
| Gate-source voltage, max. transient voltage[3)] | $V_{GS}$ | $t_p \leq 0.5$ µs, $D < 0.01$ | | -10...25 | V |
| Gate-source voltage, max. static voltage[3)] | $V_{GS}$ | | | -5...23 | V |
| Avalanche energy, single pulse | $E_{AS}$ | $I_D$ = 20 A, $V_{DD}$ = 50 V, $L$ = 1.8 mH | | 361 | mJ |
| Power dissipation, limited by $T_{vj(max)}$[2)] | $P_{tot}$ | | $T_c$ = 25 °C | 333 | W |
| | | | $T_c$ = 100 °C | 167 | |

1) Tested at Tvj=25°C, verified by design/characterization over full temperature range
2) not subject to production test - verified by design/characterization
3) **Important note:** The selection of positive and negative gate-source voltages impacts the long-term behavior of the device. The design guidelines described in Application Note AN2018-09 must be considered to ensure sound operation of the device over the planned lifetime.

**Table 3 Recommended values**

| Parameter | Symbol | Note or test condition | Values | Unit |
|---|---|---|---|---|
| Recommended turn-on gate voltage | $V_{GS(on)}$ | | 20 | V |
| Recommended turn-off gate voltage | $V_{GS(off)}$ | | 0 | V |



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**Table 4 Characteristic values**

| Parameter | Symbol | Note or test condition | | Values | | | Unit |
|---|---|---|---|---|---|---|---|
| | | | | Min. | Typ. | Max. | |
| Drain-source on-state resistance | $R_{DS(on)}$ | $I_D$ = 27 A | $T_{vj}$ = 25 °C, $V_{GS(on)}$ = 20 V | | 30 | 38 | mΩ |
| | | | $T_{vj}$ = 25 °C, $V_{GS(on)}$ = 18 V | | 33 | | |
| | | | $T_{vj}$ = 100 °C, $V_{GS(on)}$ = 20 V | | 42 | | |
| | | | $T_{vj}$ = 175 °C, $V_{GS(on)}$ = 20 V | | 60 | | |
| Gate-source threshold voltage | $V_{GS(th)}$ | $I_D$ = 8.6 mA, $V_{DS}$ = $V_{GS}$ (tested after 1 ms pulse at $V_{GS}$ = 20 V) | $T_{vj}$ = 25 °C | 3.7 | 4.4 | 5.1 | V |
| | | | $T_{vj}$ = 175 °C | | 3.6 | | |
| Zero gate-voltage drain current | $I_{DSS}$ | $V_{DS}$ = 1200 V, $V_{GS}$ = 0 V | $T_{vj}$ = 25 °C | | 0.4 | 26 | µA |
| | | | $T_{vj}$ = 175 °C | | 10 | | |
| Gate leakage current | $I_{GSS}$ | $V_{DS}$ = 0 V | $V_{GS}$ = -10 V | | | -100 | nA |
| | | | $V_{GS}$ = 25 V | | | 100 | |
| Forward transconductance | $g_{fs}$ | $I_D$ = 27 A, $V_{DS}$ = 20 V | | | 16.5 | | S |
| Short-circuit withstand time[2)] | $t_{SC}$ | $V_{DD}$ ≤ 800 V, $V_{DS,peak}$ < 1200 V, $T_{vj(start)}$ = 25 °C, $R_{G,ext}$ = 2 Ω | $V_{GS(on)}$ = 15 V | | 2.5 | | µs |
| | | | $V_{GS(on)}$ = 18 V | | 2 | | |
| | | | $V_{GS(on)}$ = 20 V | | 1.5 | | |
| Internal gate resistance | $R_{G,int}$ | $f$ = 1 MHz, $V_{AC}$ = 25 mV | | | 2.6 | | Ω |
| Input capacitance | $C_{iss}$ | $V_{DS}$ = 800 V, $V_{GS}$ = 0 V, $f$ = 100 kHz, $V_{AC}$ = 25 mV | | | 1738 | | pF |
| Output capacitance | $C_{oss}$ | $V_{DS}$ = 800 V, $V_{GS}$ = 0 V, $f$ = 100 kHz, $V_{AC}$ = 25 mV | | | 82 | | pF |
| Reverse transfer capacitance | $C_{rss}$ | $V_{DS}$ = 800 V, $V_{GS}$ = 0 V, $f$ = 100 kHz, $V_{AC}$ = 25 mV | | | 4.4 | | pF |
| $C_{oss}$ stored energy | $E_{oss}$ | $V_{DS}$ = 800 V, $V_{GS}$ = 0 V, $f$ = 100 kHz, $V_{AC}$ = 25 mV | | | 34 | | µJ |
| Total gate charge | $Q_G$ | $V_{DD}$ = 800 V, $I_D$ = 27 A, $V_{GS}$ = 0/20 V, turn-on pulse | | | 57 | | nC |
| Plateau gate charge | $Q_{GS(pl)}$ | $V_{DD}$ = 800 V, $I_D$ = 27 A, $V_{GS}$ = 0/20 V, turn-on pulse | | | 15 | | nC |
| Gate-drain charge | $Q_{GD}$ | $V_{DD}$ = 800 V, $I_D$ = 27 A, $V_{GS}$ = 0/20 V, turn-on pulse | | | 10 | | nC |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}$ = 800 V, $I_D$ = 27 A, $V_{GS}$ = 0/20 V, $R_{G,ext}$ = 2 Ω, $L_\sigma$ = 20 nH, diode: body diode at $V_{GS}$ = 0 V | $T_{vj}$ = 25 °C | | 8.3 | | ns |
| | | | $T_{vj}$ = 175 °C | | 8.2 | | |

**(table continues...)**



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**Table 4 (continued) Characteristic values**

| Parameter | Symbol | Note or test condition | | Values | | | Unit |
|---|---|---|---|---|---|---|---|
| | | | | Min. | Typ. | Max. | |
| Rise time | $t_r$ | $V_{DD}$ = 800 V, $I_D$ = 27 A, $V_{GS}$ = 0/20 V, $R_{G,ext}$ = 2 Ω, $L_\sigma$ = 20 nH, diode: body diode at $V_{GS}$ = 0 V | $T_{vj}$ = 25 °C | | 7.6 | | ns |
| | | | $T_{vj}$ = 175 °C | | 9.2 | | |
| Turn-off delay time | $t_{d(off)}$ | $V_{DD}$ = 800 V, $I_D$ = 27 A, $V_{GS}$ = 0/20 V, $R_{G,ext}$ = 2 Ω, $L_\sigma$ = 20 nH, diode: body diode at $V_{GS}$ = 0 V | $T_{vj}$ = 25 °C | | 18.6 | | ns |
| | | | $T_{vj}$ = 175 °C | | 19.8 | | |
| Fall time | $t_f$ | $V_{DD}$ = 800 V, $I_D$ = 27 A, $V_{GS}$ = 0/20 V, $R_{G,ext}$ = 2 Ω, $L_\sigma$ = 20 nH, diode: body diode at $V_{GS}$ = 0 V | $T_{vj}$ = 25 °C | | 8.5 | | ns |
| | | | $T_{vj}$ = 175 °C | | 8.7 | | |
| Turn-on energy | $E_{on}$ | $V_{DD}$ = 800 V, $I_D$ = 27 A, $V_{GS}$ = 0/20 V, $R_{G,ext}$ = 2 Ω, $L_\sigma$ = 20 nH, diode: body diode at $V_{GS}$ = 0 V | $T_{vj}$ = 25 °C | | 179 | | µJ |
| | | | $T_{vj}$ = 175 °C | | 255 | | |
| Turn-off energy | $E_{off}$ | $V_{DD}$ = 800 V, $I_D$ = 27 A, $V_{GS}$ = 0/20 V, $R_{G,ext}$ = 2 Ω, $L_\sigma$ = 20 nH, diode: body diode at $V_{GS}$ = 0 V | $T_{vj}$ = 25 °C | | 57 | | µJ |
| | | | $T_{vj}$ = 175 °C | | 56 | | |
| Total switching energy | $E_{tot}$ | $V_{DD}$ = 800 V, $I_D$ = 27 A, $V_{GS}$ = 0/20 V, $R_{G,ext}$ = 2 Ω, $L_\sigma$ = 20 nH, diode: body diode at $V_{GS}$ = 0 V | $T_{vj}$ = 25 °C | | 236 | | µJ |
| | | | $T_{vj}$ = 175 °C | | 311 | | |
| Virtual junction temperature | $T_{vj}$ | | | -55 | | 175 | °C |

***Note**: Characteristics at $T_{vj}$ = 25°C, unless otherwise specified.*

# 3 Body diode (MOSFET)

**Table 5 Maximum rated values**

| Parameter | Symbol | Note or test condition | | Values | Unit |
|---|---|---|---|---|---|
| Drain-source voltage[1)] | $V_{DSS}$ | $T_{vj}$ = -55...175 °C | | 1200 | V |
| Continuous reverse drain current for $R_{th(j\text{-}c,max)}$, limited by $T_{vj(max)}$[2)] | $I_{SDC}$ | | $T_c$ = 25 °C | 60 | A |
| | | | $T_c$ = 100 °C | 36 | |

**(table continues...)**



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**Table 5 (continued) Maximum rated values**

| Parameter | Symbol | Note or test condition | | Values | Unit |
|---|---|---|---|---|---|
| Peak reverse drain current, $t_p$ limited by $T_{vj(max)}$ | $I_{SM}$ | | $V_{GS}$ = 0 V | 60 | A |
| | | | -5 V < $V_{GS}$ < 0 V, $t_p$ < 0.3 µs | 80 | |
| | | | -5 ≤ $V_{GS}$ ≤ 0 V, Tvj ≤ 175°C; $t_p$ ≤ 0.3 ms for accumulated conduction time < 5 s or $t_p$ ≤ 1 ms for accumulated conduction time < 2.5 s[3)] | 207 | |

*1)* Tested at Tvj=25°C, verified by design/characterization over full temperature range
*2)* not subject to production test - verified by design/characterization
*3)* combination of tp and Ism should not lead to Tvj(max) > 175°C

**Table 6 Characteristic values**

| Parameter | Symbol | Note or test condition | | Values | | | Unit |
|---|---|---|---|---|---|---|---|
| | | | | Min. | Typ. | Max. | |
| Drain-source reverse voltage | $V_{SD}$ | $I_{SD}$ = 27 A | $T_{vj}$ = 25 °C | | 3.9 | 5 | V |
| | | | $T_{vj}$ = 100 °C | | 3.8 | | |
| | | | $T_{vj}$ = 175 °C | | 3.7 | | |
| MOSFET forward recovery charge | $Q_{fr}$ | $V_{DD}$ = 800 V, $I_{SD}$ = 27 A, $V_{GS}$ = 0 V, $-di_{SD}/dt$ = 2000 A/µs, $Q_{fr}$ includes also $Q_C$ | $T_{vj}$ = 25 °C | | 175 | | nC |
| | | | $T_{vj}$ = 175 °C | | 339 | | |
| MOSFET peak forward recovery current | $I_{frm}$ | $V_{DD}$ = 800 V, $I_{SD}$ = 27 A, $V_{GS}$ = 0 V, $-di_{SD}/dt$ = 2000 A/µs, $Q_{fr}$ includes also $Q_C$ | $T_{vj}$ = 25 °C | | 13.5 | | A |
| | | | $T_{vj}$ = 175 °C | | 16.6 | | |
| Virtual junction temperature | $T_{vj}$ | | | -55 | | 175 | °C |



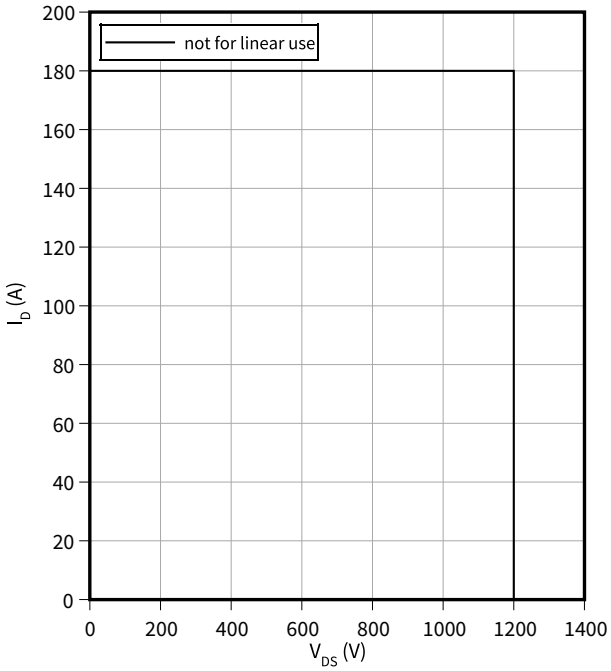
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# 4 Characteristics diagrams

**Reverse bias safe operating area (RBSOA)**

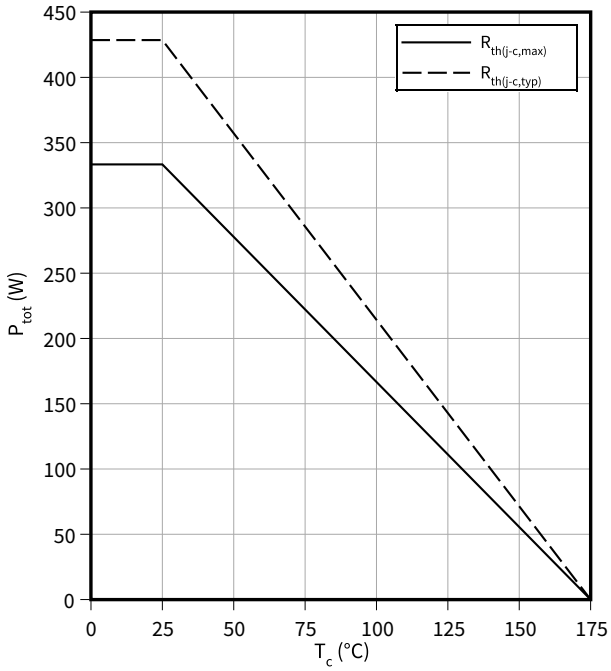
$I_D = f(V_{DS})$

$T_{vj} \leq 175$ °C, $V_{GS} = 0/20$ V, $T_c = 25$ °C



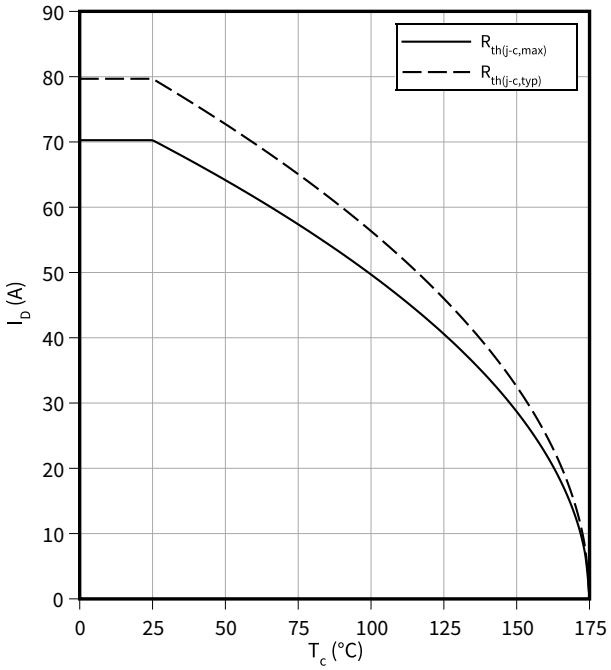

**Power dissipation as a function of case temperature**

$P_{tot} = f(T_c)$




**Maximum DC drain to source current as a function of case temperature**

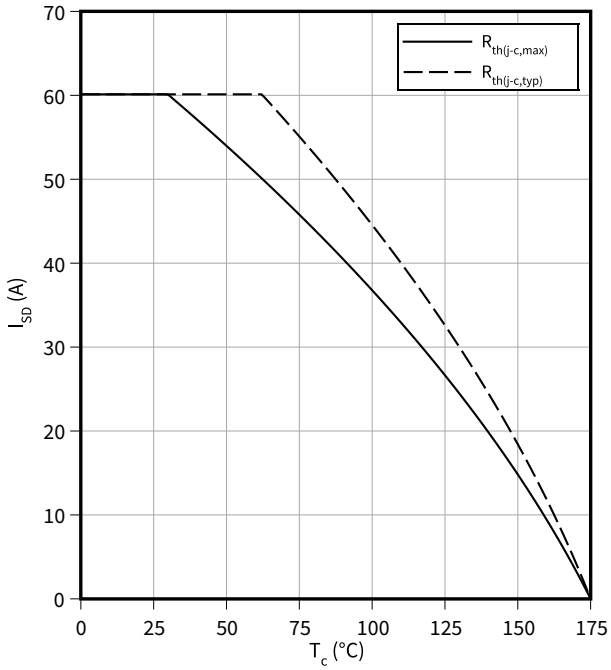
$I_D = f(T_c)$




**Maximum source to drain current as a function of case temperature**

$I_{SD} = f(T_c)$

$V_{GS} = 0$ V

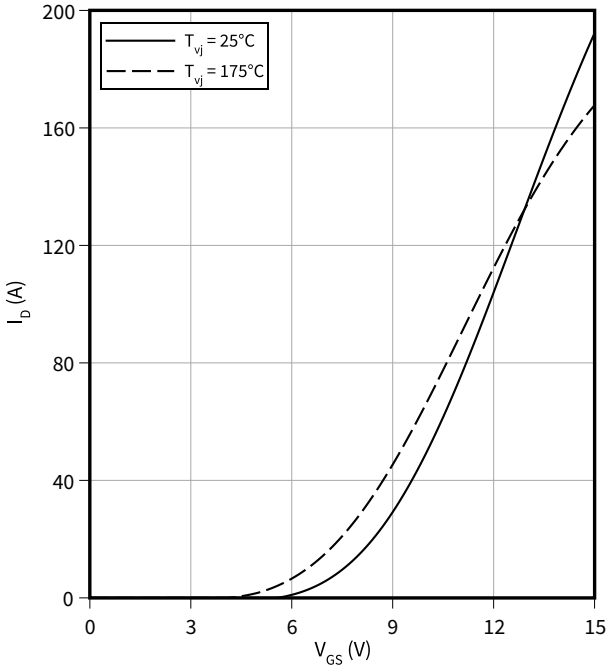





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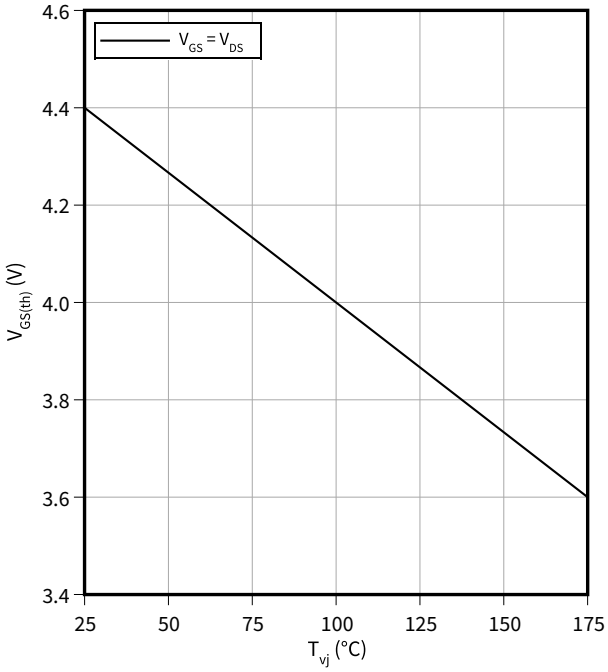
### Typical transfer characteristic

$I_D = f(V_{GS})$
$V_{DS}$ = 20 V, $t_p$ = 20 µs



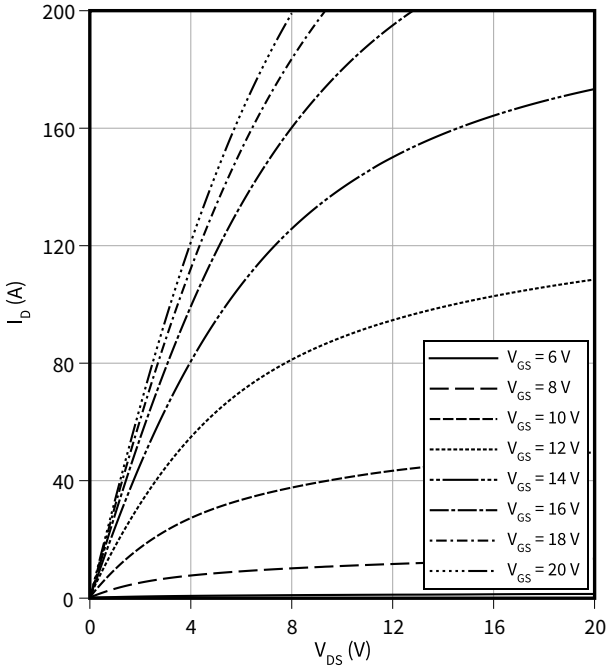

### Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$
$I_D$ = 8.6 mA



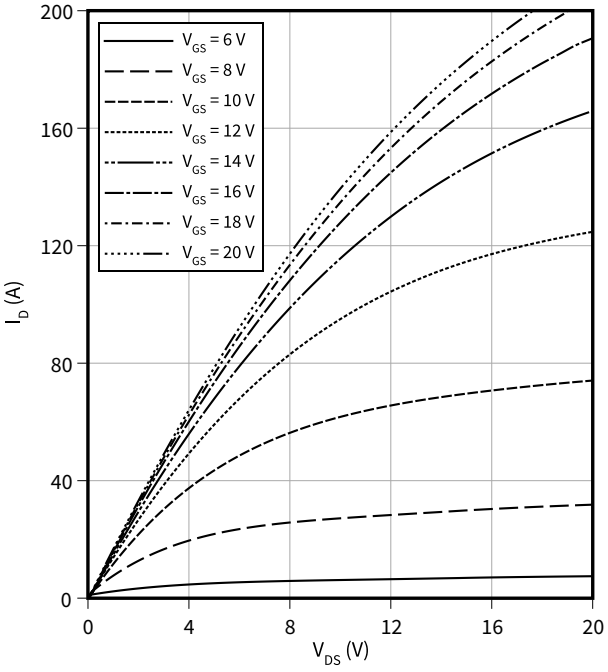

### Typical output characteristic, $V_{GS}$ as parameter

$I_D = f(V_{DS})$
$T_{vj}$ = 25 °C, $t_p$ = 20 µs




### Typical output characteristic, $V_{GS}$ as parameter

$I_D = f(V_{DS})$
$T_{vj}$ = 175 °C, $t_p$ = 20 µs

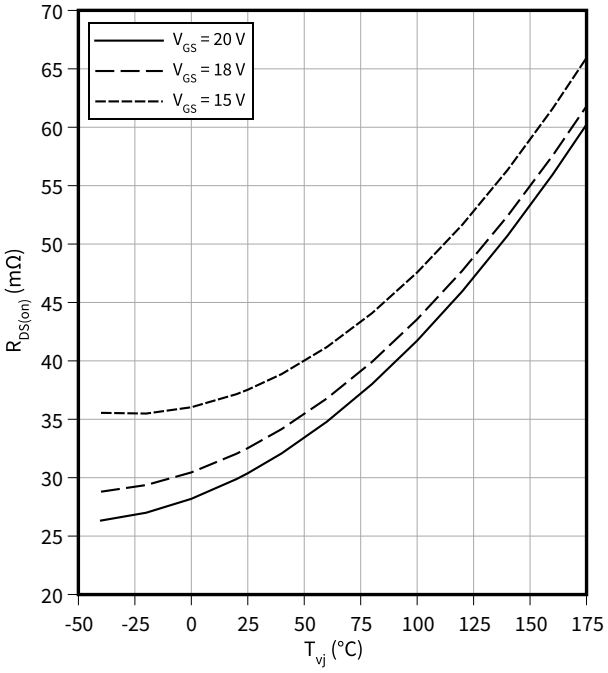





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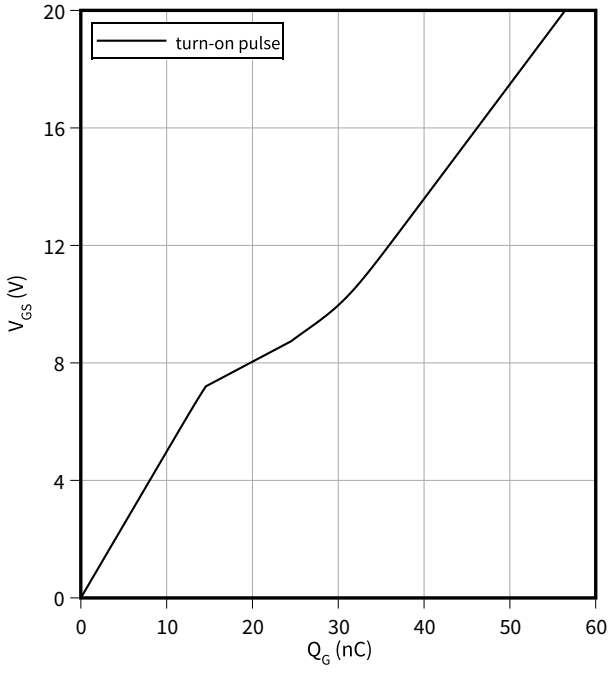
### Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$
$I_D = 27$ A



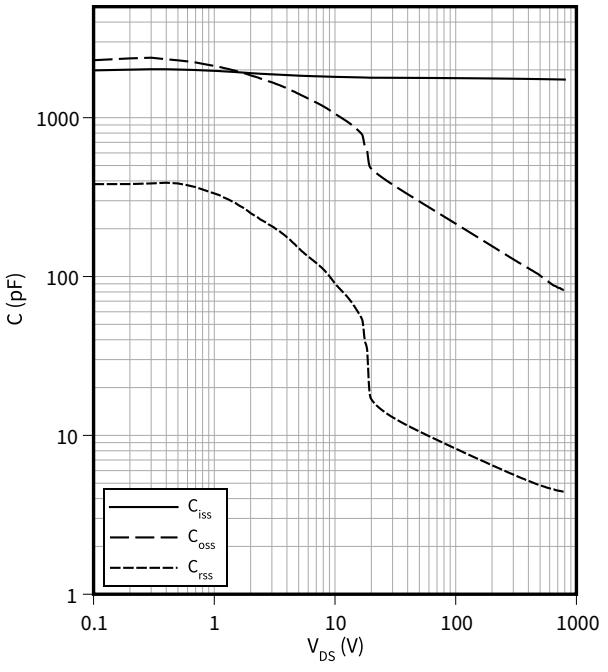

### Typical gate charge

$V_{GS} = f(Q_G)$
$I_D = 27$ A, $V_{DS} = 800$ V



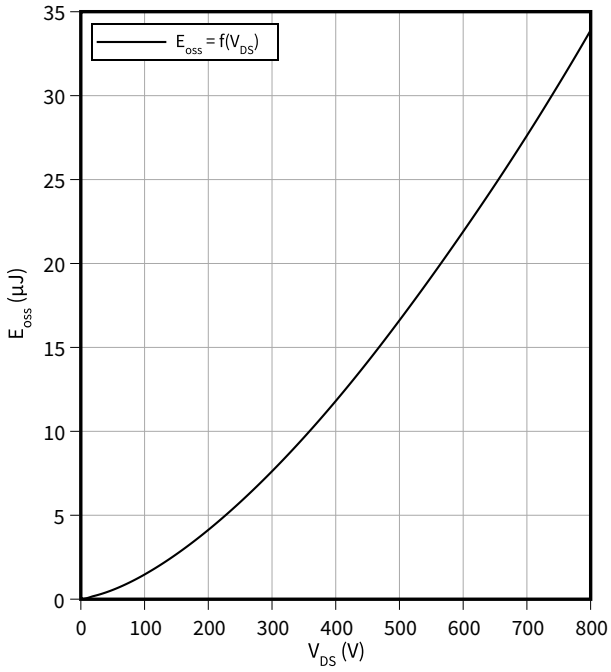

### Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$
$f = 100$ kHz, $V_{GS} = 0$ V




### Typical $C_{oss}$ stored energy

$E_{oss} = f(V_{DS})$
$f = 100$ kHz, $V_{GS} = 0$ V



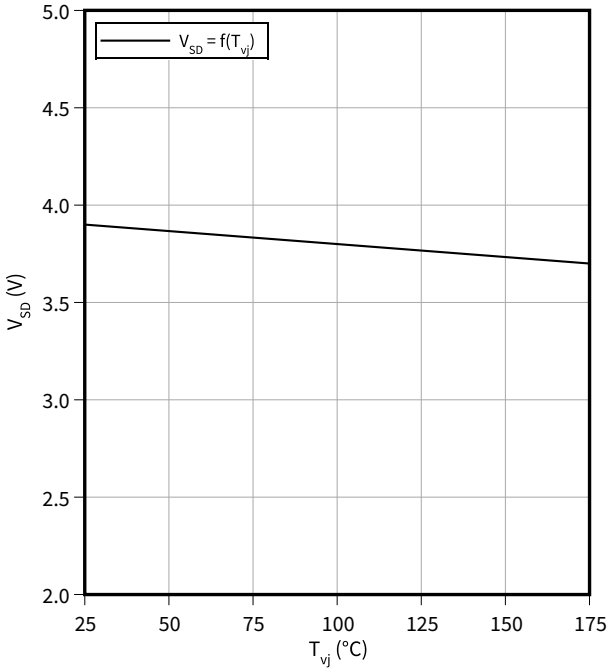



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### Typical reverse drain voltage as function of junction temperature

$V_{SD} = f(T_{vj})$

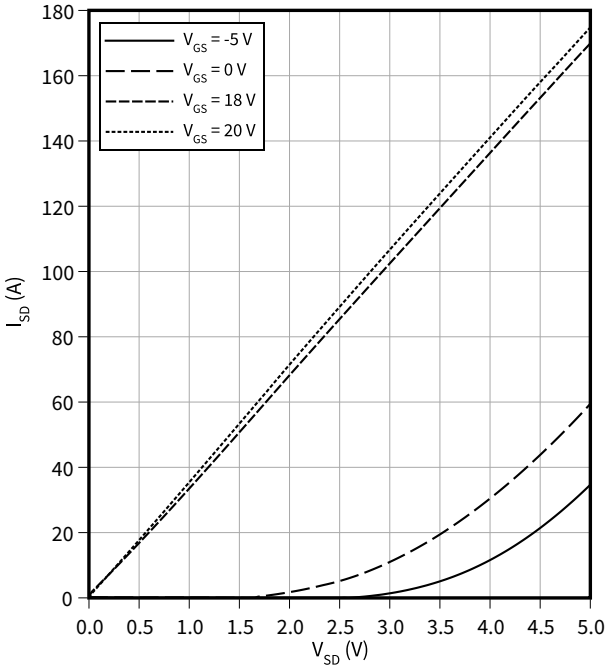
$I_{SD}$ = 27 A, $V_{GS}$ = 0 V




### Typical reverse drain current as function of reverse drain voltage, $V_{GS}$ as parameter

$I_{SD} = f(V_{SD})$

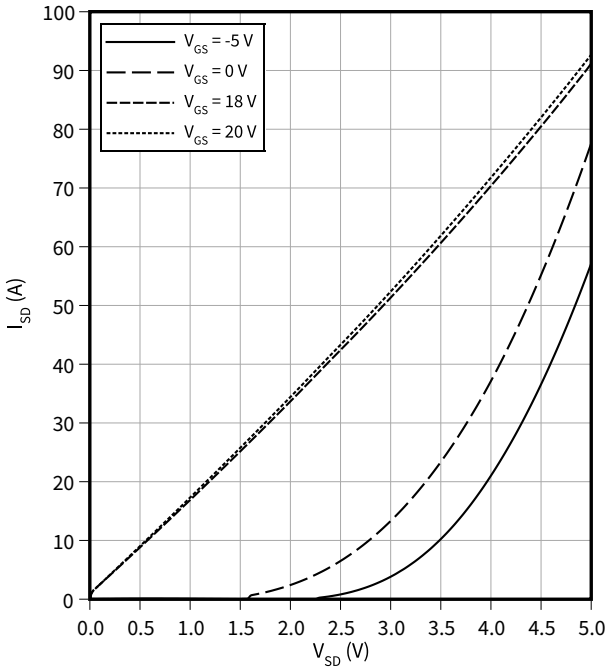
$T_{vj}$ = 25 °C, $t_p$ = 20 µs




### Typical reverse drain current as function of reverse drain voltage, $V_{GS}$ as parameter

$I_{SD} = f(V_{SD})$

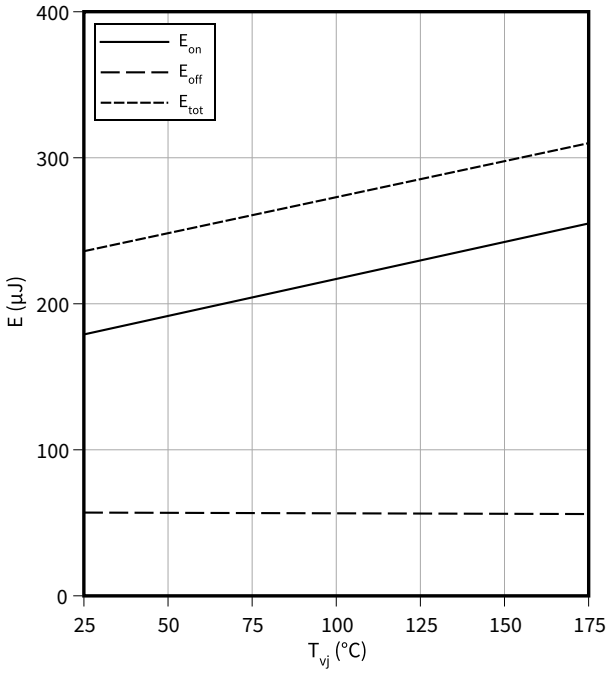
$T_{vj}$ = 175 °C, $t_p$ = 20 µs




### Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS}$ = 0 V

$E = f(T_{vj})$

$V_{GS}$ = 0/20 V, $I_D$ = 27 A, $R_{G,ext}$ = 2 Ω, $V_{DD}$ = 800 V



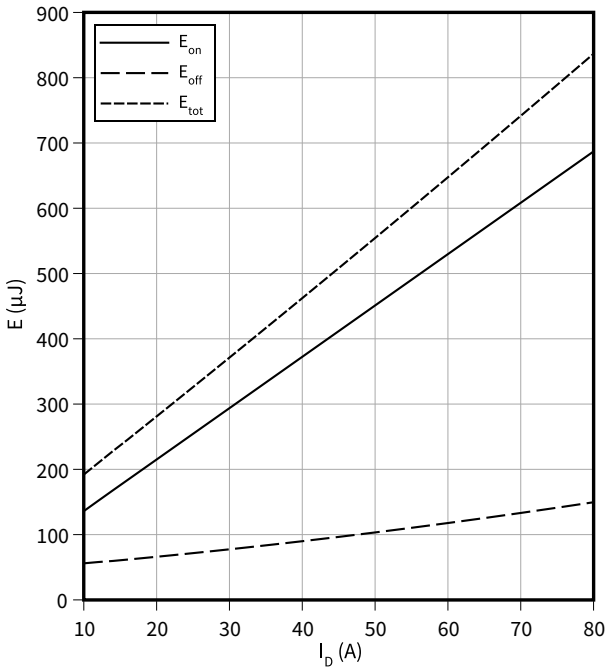



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**Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS}$ = 0 V**

E = f($I_D$)

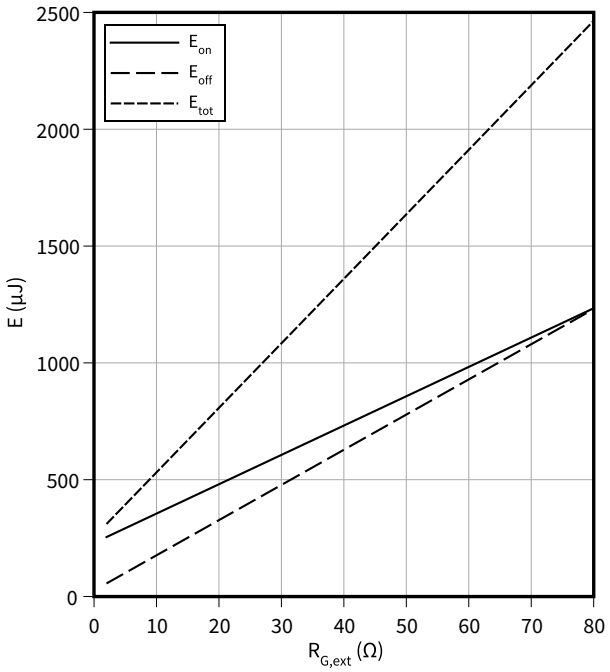
$V_{GS}$ = 0/20 V, $T_{vj}$ = 175 °C, $R_{G,ext}$ = 2 Ω, $V_{DD}$ = 800 V




**Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS}$ = 0 V**

E = f($R_{G,ext}$)

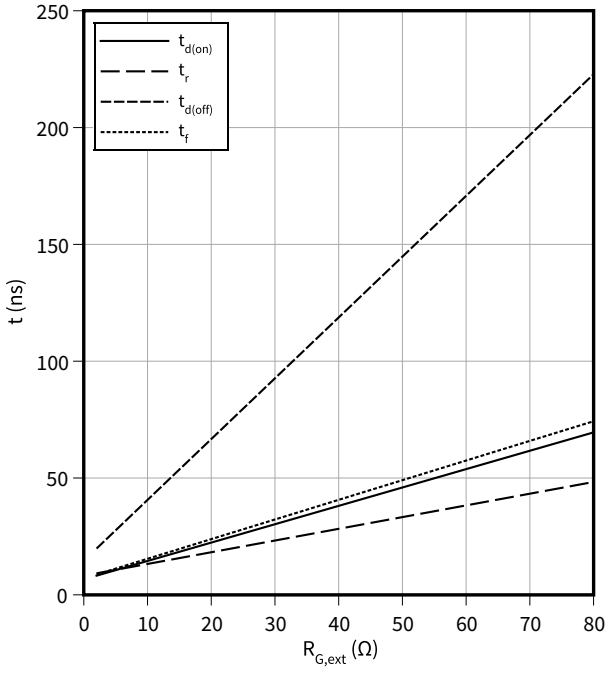
$V_{GS}$ = 0/20 V, $I_D$ = 27 A, $T_{vj}$ = 175 °C, $V_{DD}$ = 800 V




**Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS}$ = 0 V**

t = f($R_{G,ext}$)

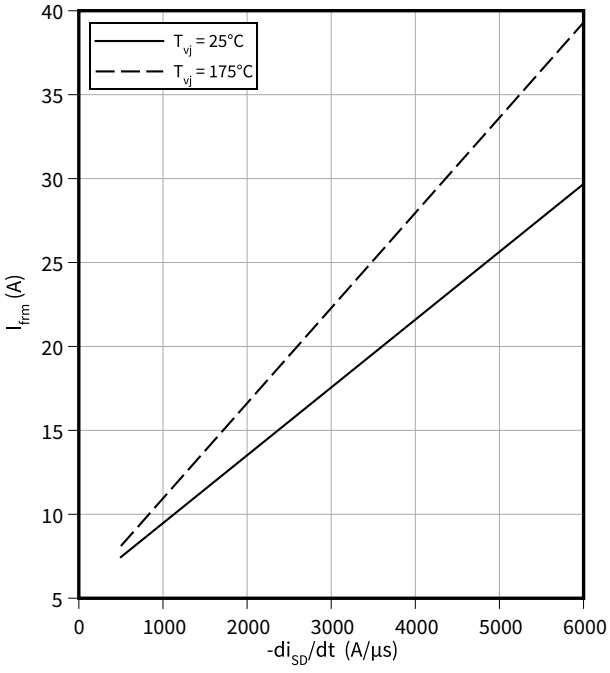
$V_{GS}$ = 0/20 V, $I_D$ = 27 A, $T_{vj}$ = 175 °C, $V_{DD}$ = 800 V




**Typical MOSFET peak forward recovery current as a function of reverse drain current slope**

$I_{frm}$ = f(-$di_{SD}$/dt )

$I_{SD}$ = 27 A, $V_{DD}$ = 800 V, $V_{GS}$ = 0/20 V

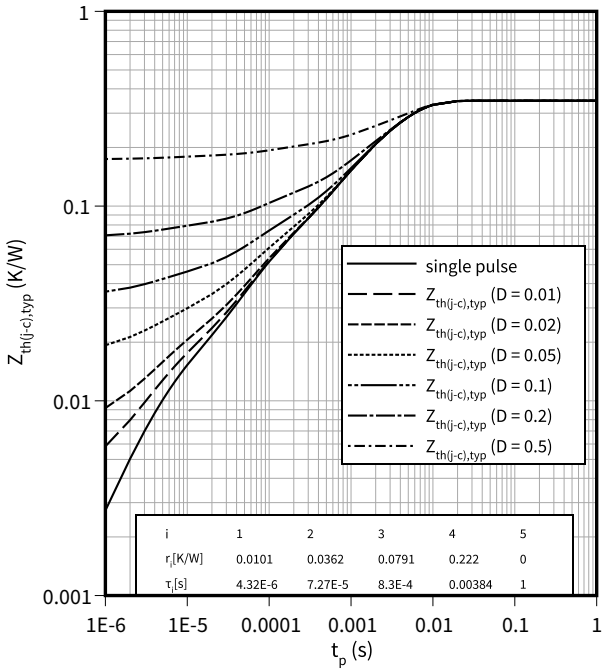





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### Typ. transient thermal impedance (MOSFET/diode)

$Z_{th(j-c),typ} = f(t_p)$
$D = t_p/T$

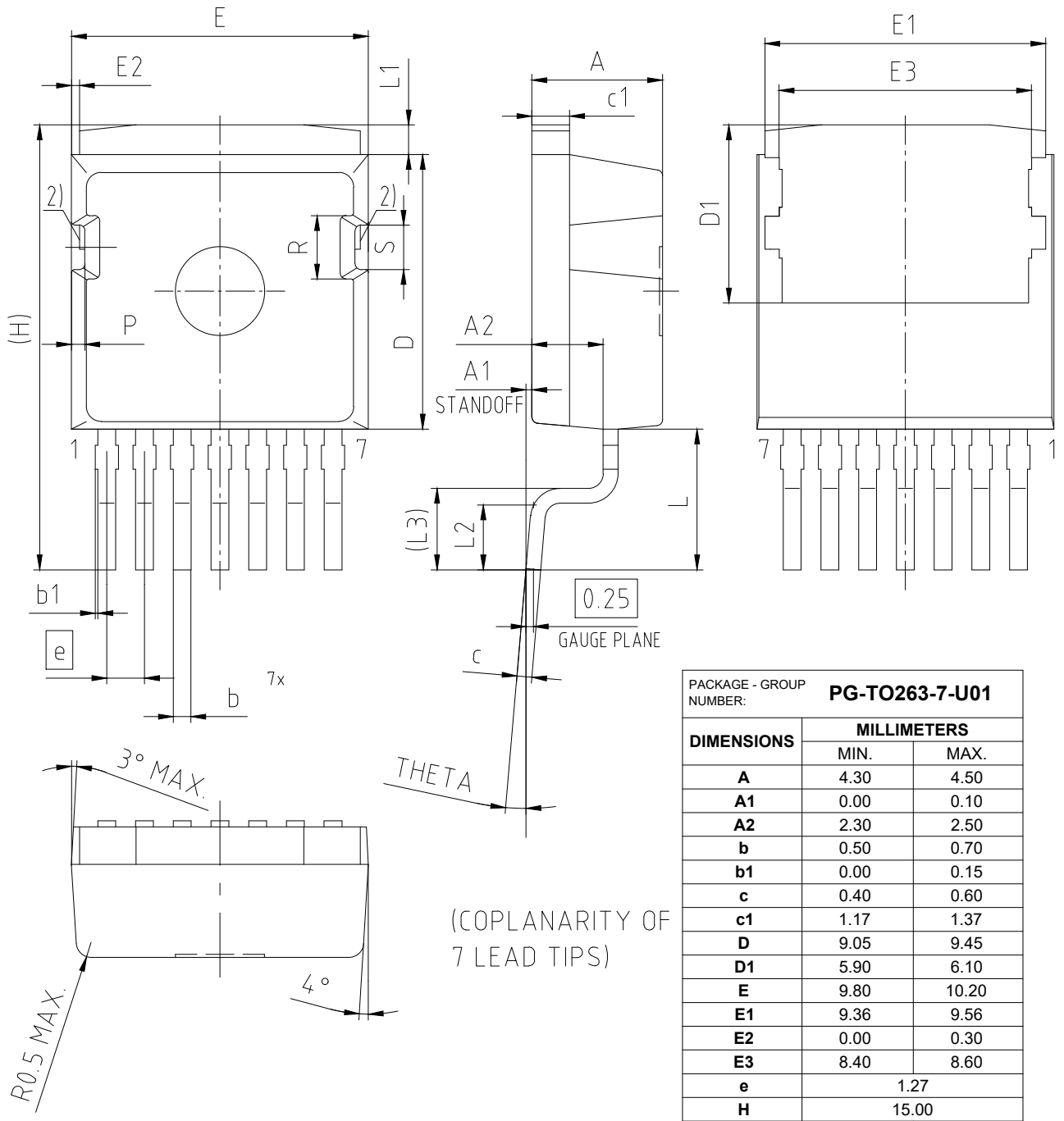



| i | 1 | 2 | 3 | 4 | 5 |
|---|---|---|---|---|---|
| $r_i$[K/W] | 0.0101 | 0.0362 | 0.0791 | 0.222 | 0 |
| $\tau_i$[s] | 4.32E-6 | 7.27E-5 | 8.3E-4 | 0.00384 | 1 |



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# 5 Package outlines




| PACKAGE - GROUP NUMBER: | PG-TO263-7-U01 | |
|---|---|---|
| **DIMENSIONS** | **MILLIMETERS** | |
| | MIN. | MAX. |
| **A** | 4.30 | 4.50 |
| **A1** | 0.00 | 0.10 |
| **A2** | 2.30 | 2.50 |
| **b** | 0.50 | 0.70 |
| **b1** | 0.00 | 0.15 |
| **c** | 0.40 | 0.60 |
| **c1** | 1.17 | 1.37 |
| **D** | 9.05 | 9.45 |
| **D1** | 5.90 | 6.10 |
| **E** | 9.80 | 10.20 |
| **E1** | 9.36 | 9.56 |
| **E2** | 0.00 | 0.30 |
| **E3** | 8.40 | 8.60 |
| **e** | 1.27 | |
| **H** | 15.00 | |
| **L** | 4.20 | 5.20 |
| **L1** | 0.70 | 1.30 |
| **L2** | 1.70 | 2.30 |
| **L3** | 2.70 | |
| **P** | 0.35 | 0.55 |
| **R** | 2.03 | 2.23 |
| **S** | 1.40 | 1.60 |
| **THETA** | 0.00° | 8.00° |

**Figure 1**



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# 6 Testing conditions

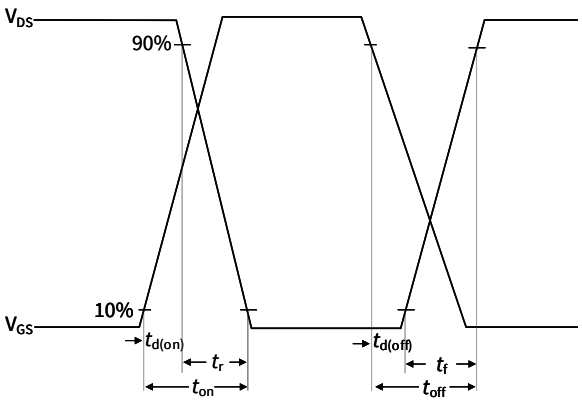



Figure A. **Definition of switching times**

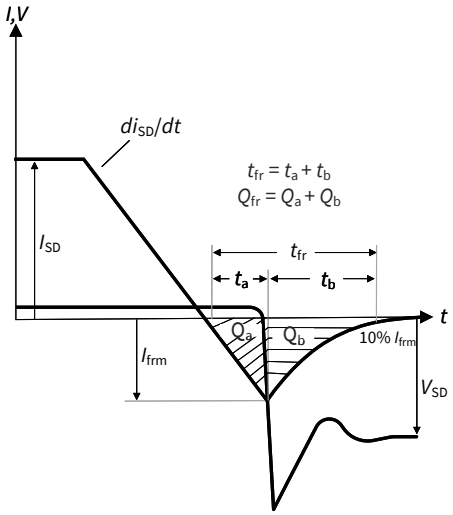



Figure B. **Definition of body diode switching characteristics**

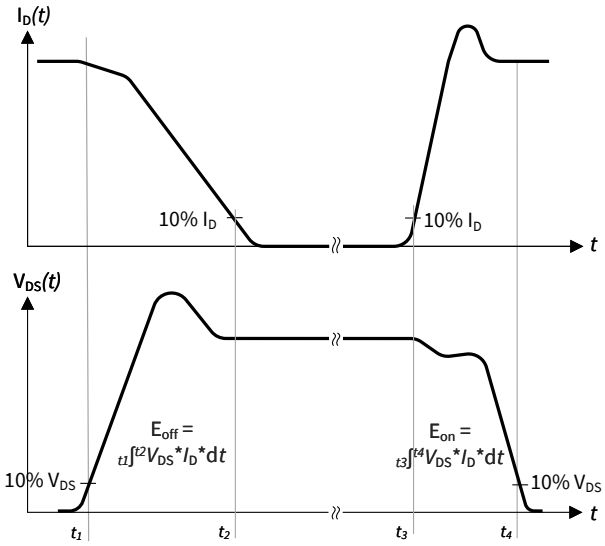



Figure C. **Definition of switching losses**

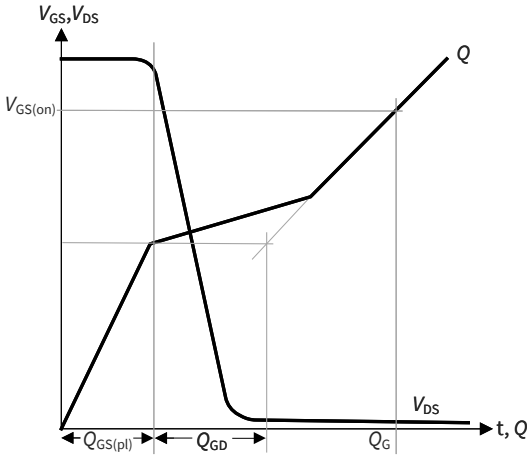



Figure D. **Definition of QGD**

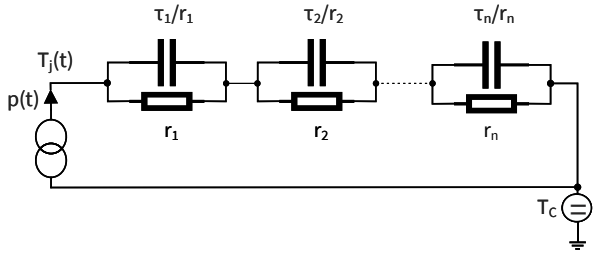



Figure E. **Thermal equivalent circuit**

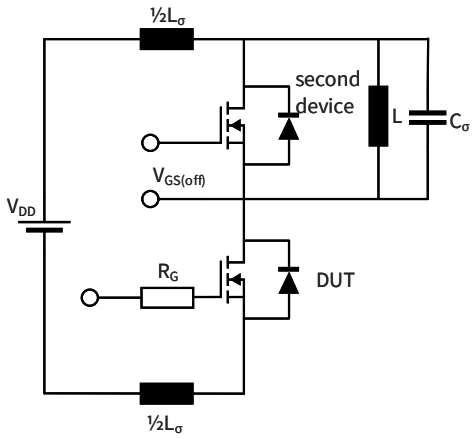



Figure F. **Dynamic test circuit**
Parasitic inductance $L_\sigma$,
Parasitic capacitor $C_\sigma$,

**Figure 2**



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## Revision history

| Document revision | Date of release | Description of changes |
|---|---|---|
| 0.10 | 2022-12-08 | Preliminary datasheet |
| 1.00 | 2023-06-23 | Final datasheet |
| 1.10 | 2024-04-02 | Updated table values: Rdson. Vgsth, Idss, gfs, tdon, tr, tdoff, tf, Eon, Eoff, Etot,Qfr, Ifrm, Isdc, Ism<br>Updated graphs: ISD=f(Tc), IDS = f(VGS), VGS(th) = f(Tvj), IDS = f(VDS), RDS(on) = f(Tvj), ISD = f(VSD), E = f(Tvj), E = f(RG,ext), t = f(RG,ext), Ifrm = f(-diSD/dt )<br>Added new graphs: E = f(ID), Eoss = f(VDS)<br>No change to the product, new values based on additional characterization |
| 1.20 | 2024-11-13 | Updated features: “Minimal creepage distance 5.85mm (material group II) to fit 800V applications without coating” changed to “Creepage distance of 5.8mm (material group II) to fit 800V applications”<br>Updated package from PG-TO263-7-HV-ND5.8 to PG-TO263-7-U01 |
| 1.30 | 2026-02-19 | Extended Ism limits at additional conditions, Zth(max) graph replaced with Zth(typ) graph |



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**Edition 2026-02-19**

**Published by**

**Infineon Technologies AG**

**81726 Munich, Germany**

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**Document reference**
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